

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Leonard Forbes et al.

Examiner:

Johannes P Mondt

Serial No.:

09/691004

Group Art Unit:

2826

Filed:

October 18, 2000

Docket:

303.324US4

Title:

TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND

METHODS OF FABRICATION AND USE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

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Title: TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

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Date 2 December 2003

By

Robert E. Mates Reg. No. 35,271

<u>CERTIFICATE UNDER 37 CFR 1.8:</u> The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 2nd day of December, 2003.

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Signature

PATENT

S/N 09/691006 IN THE UNIXED STATES PATENT AND TRADEMARK OFFICE

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COMMUNICATION CONCERNING RELATED APPLICATION(S)

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u> 09/256643	Filing Date February 23, 1999	Attorney Docket 303.324US2	Title TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE END METHODS OF FABRICATION AND USE
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
08/903486	July 29, 1997	303.326US1	SILICON CARBIDE GATE TRANSISTOR
09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR
08/902132 5886368	July 29, 1997	303.353US1	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294 6309907	August 21, 1998	303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE

RECEIVEL

Serial Number: 09/691004

Filing Date: October 18, 2000 Title: TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE Page 2 Dkt: 303.324US4

DEAPROM HAVING AMORPHOUS 303.354US1 08/902843 July 29, SILICON CARBIDE GATE 1997 **INSULATOR** METHOD FOR OPERATING A 303.354US2 09/135413 August 14, DEAPROM HAVING AN 1998 AMORPHOUS SILICON CARBIDE **GATE INSULATOR** DEAPROM HAVING AMORPHOUS August 14, 303.354US3 09/134713 SILICON CARBIDE GATE 1998 **INSULATOR** DEAPROM AND TRANSISTOR WITH 303.355US1 08/902098 July 29, GALLIUM NITRIDE OR GALLIUM 1997 6031263 ALUMINUM NITRIDE GATE DEAPROM AND TRANSISTOR WITH 303.355US2 09/140978 August 27, GALLIUM NITRIDE OR GALLIUM 6307775 1998 ALUMINUM NITRIDE GATE DEAPROM AND TRANSISTOR WITH 303.355US3 August 27, 09/141392 GALLIUM NITRIDE OR GALLIUM 1998 6249020 ALUMINUM NITRIDE GATE DEAPROM AND TRANSISTOR WITH 303.355US4 09/883795 June 18, GALLIUM NITRIDE OR GALLIUM 2001 ALUMINUM NITRIDE GATE DEAPROM AND TRANSISTOR WITH 303.355US5 10/047181 October 23, GALLIUM NITRIDE OR GALLIUM 2001 ALUMINUM NITRIDE GATE MEMORY DEVICE 08/902133 July 29, 303.356US1 1997 DYNAMIC ELECTRICALLY 10/231687 August 29, 303.356US2 ALTERABLE PROGRAMMABLE 2002 READ ONLY MEMORY DEVICE CARBURIZED SILICON GATE 08/903453 July 29, 303.378US1 INSULATORS FOR INTEGRATED 1997 **CIRCUITS** CARBURIZED SILICON GATE 303.378US2 09/258467 February

Page 3 Dkt: 303.324US4

Serial Number: 09/691004

Filing Date: October 18, 2000

Title: TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE

	26, 1999		INSULATORS FOR INTEGRATED CIRCUITS
09/650553	August 30, 2000	303.378US3	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
10/461593	June 11, 2003	303.356US3	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE

Respectfully submitted,

LEONARD FORBES ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. Box 2938

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Dated December 2003

By

Robert E. Mates

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Signature

PTO/SB/084(10-01)
Approved for use through 10/31/2022, 0MB 651-0031
US Patent & Trademerk Office: U.S. DEPARTMENT OF COMMERCE

The Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Complete if Known 09/691004 **Application Number** October 18, 2000 Filing Date

Mondt, Johannes

Forbes, Leonard **First Named Inventor** 2826 **Group Art Unit**

Attorney Docket No: 303.324US4

	US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate	
	US-4,736,317	04/05/1988	Hu, M., et al.	364	200	07/17/1985	
-	US-4,980,303	12/25/1990	Yamauchi, T.	437	31	08/18/1988	
	US-5,189,504	02/23/1993	Nakayama, S., et al.	257	422	01/30/1992	
	US-5,336,361	08/09/1994	Tamura, A., et al.	438	767	11/02/1992	
14	US-5,360,491	11/01/1994	Carey, P G., et al.	136	256	04/07/1993	
1	US-5,367,306	11/22/1994	Hollon, , et al.	342	386	06/04/1993	
	US-5,409,501	04/25/1995	Zauns-Huber, R., et al.	8	94.29	07/06/1992	
	US-5,425,860	06/20/1995	Truher, J. B., et al.	204	192.23	04/07/1993	
	US-5,623,160	04/22/1997	Liberkowski, J. B.	257	621	09/14/1995	
	US-5,990,531	11/23/1999	Taskar, N. R., et al.	257	410	11/12/1997	
	US-6,100,193	08/08/2000	Suehiro, S., et al.	438	685	09/24/1997	
	US-6,166,768	12/26/2000	Fossum, , et al.	348	308	01/22/1997	
	US-6,365,919	04/02/2002	Tihanyi, J., et al.	257	77	07/11/2000	

Examiner Name

	FOREIGN PATENT DOCUMENTS					
Examiner Foreign Document No Initials*		Publication Date Name of Patentee or Applicant of cited Document		Class	Subclass	T ²
	JP-60-024678	02/07/1985	Akio, Nakatani	G06 K	9/36	

	OTHER	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		ECEIVED LOGY CENTER 2800

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE

STATEMENT BY APPLICANT